


Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	31	flash same update same version same compar\$3	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 15:21
L2	29	update near3 parameter with flash	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 15:21
L1	49	update with flash with parameter	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 15:02
S71	38	flash with characteri\$6 with (select\$3 optim\$7) with \$2writ\$3	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 15:01
S68	593	flash with characteri\$6 with (select\$3 optim\$7)	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:54
S70	0	flash with characteri\$6 with (select\$3 optim\$7) with update	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:53
S69	4	flash with characteri\$6 with (select\$3 optim\$7) with lot	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:53
S67	6	flash with characterization with (select\$3 optim\$7)	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:52
S66	0	flash with characterization same updat\$3	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:48
S65	0	flash with characterization same update	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:48
S64	167	flash with characterization	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:48
S63	1	("5434094").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:48
S62	2	("6458611").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/26 13:47
S61	22	S58 and update	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:46

S60	0	S58 and S59	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:45
S59	2111	flash with update	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:45
S58	3787	(438/17).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/26 13:45
S57	17	flash with test with update	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:45
S56	16	flash with parameter with rewrit\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:39
S55	0	flash with parameter with rewrit\$3 with depend\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:31
S54	2	flash with voltage with rewrit\$3 with depend\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:31
S53	1	flash with voltage with rewrit\$3 with optim\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:30
S52	6	flash with voltage with rewrit\$3 with select\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:28
S51	1	flash with voltage with rewrit\$3 with update	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:25

S49	4	flash with voltage with rewrit\$3 with var\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:24
S48	267	flash with voltage with rewrit\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:24
S47	18221	flash with voltage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:21
S46	282558	flash withvoltage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:21
S45	27447	flash same voltage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:21
S44	3	flash same voltag	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:21
S43	21	characteristic with lot same flash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:21
S42	14	characteristic with lot same update	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 12:37
S41	2	characteristic with lot with test same update	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 12:37
S40	1	characteristic with lot with test same flash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 12:36

S39	151	characteristic with lot with test	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 12:36
S38	1	"6456554".pn.	DERWENT	OR	ON	2005/05/26 12:35
S37	2	"2000021694"	DERWENT	OR	ON	2005/05/26 12:35
S32	10	characteristic with lot with test	DERWENT	OR	ON	2005/05/26 12:35
S36	1	JP2000021694A	DERWENT	OR	ON	2005/05/26 12:32
S35	0	"Manufacture specification indication arrangement in semiconductor device - has information recording area formed on semiconductor chip, in which data relating to manufacture lot and serial number of wafer are recorded"	DERWENT	OR	ON	2005/05/26 12:32
S34	0	"02000021694"	DERWENT	OR	ON	2005/05/26 12:31
S33	0	"02000021694".oref.	DERWENT	OR	ON	2005/05/26 12:31
S1	0	2000-0040430	DERWENT	OR	ON	2005/05/26 12:22


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[PDF] [Application Note-07 DATA PROTECTION METHOD OF W28XXX SERIES FLASH](#)

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... To protect any data against inadvertent **rewriting** under such situation, ... supply **voltage**, the **flash memory** is disabled and the erasing/writing in all ...
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... on the power supply or resetting by the #RESET pin, the **flash memory** usually enters a ... **rewriting** due to the command mis-recognition can be prevented. ...
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Frequently-asked question about **flash memory** for F2MC-16LX Family microcontroller. ...

The Fujitsu's **Flash** microcomputer can perform **rewriting** sufficiently ...

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... enable low-**voltage** read and write operations, making this an ideal **memory** for ...

Rewriting data on Flash Memory requires that data must be erased by ...

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[64-Mbit AND-Type Flash Memory](#)

... this **flash memory** device allows the high **voltage** required for **rewriting** to be generated on the chip, so the chip can run on a single 3.3-V power supply. ...

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... wear leveling function can increase the life span of **rewriting** of **flash memory**. ...

Memory. Structure. Operation. **Voltage**. Package. Price for 100000 ...

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... it is necessary to make the threshold **voltage** of the **memory** cells greater ... With this

FLASH IP an interface circuit for **rewriting** the following three ...

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... function can increase the life span of **rewriting** of **flash memory**. ... The product of operation **voltage** 1.8 V and x 16 bits is also equipped with a ...

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